



Welcome to [E-XFL.COM](https://www.e-xfl.com)

### What is "[Embedded - Microcontrollers](#)"?

"[Embedded - Microcontrollers](#)" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

### Applications of "[Embedded - Microcontrollers](#)"

#### Details

Product Status	Obsolete
Core Processor	dsPIC
Core Size	16-Bit
Speed	30 MIPS
Connectivity	CANbus, I <sup>2</sup> C, SPI, UART/USART
Peripherals	Brown-out Detect/Reset, LVD, POR, PWM, WDT
Number of I/O	52
Program Memory Size	132KB (44K x 24)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	6K x 8
Voltage - Supply (Vcc/Vdd)	2.5V ~ 5.5V
Data Converters	A/D 16x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-TQFP
Supplier Device Package	64-TQFP (14x14)
Purchase URL	<a href="https://www.e-xfl.com/product-detail/microchip-technology/dspic30f6011t-30i-pf">https://www.e-xfl.com/product-detail/microchip-technology/dspic30f6011t-30i-pf</a>

# dsPIC30F Flash Programming Specification

## 5.5.3 PROGRAMMING VERIFICATION

Once code memory is programmed, the contents of memory can be verified to ensure that programming was successful. Verification requires code memory to be read back and compared against the copy held in the programmer's buffer.

The `READP` command can be used to read back all the programmed code memory.

Alternatively, you can have the programmer perform the verification once the entire device is programmed using a checksum computation, as described in [Section 6.8 "Checksum Computation"](#).

## 5.6 Data EEPROM Programming

### 5.6.1 OVERVIEW

The panel architecture for the data EEPROM memory array consists of 128 rows of sixteen 16-bit data words. Each panel stores 2K words. All devices have either one or no memory panels. Devices with data EEPROM provide either 512 words, 1024 words or 2048 words of memory on the one panel (see [Table 5-3](#)).

**TABLE 5-3: DATA EEPROM SIZE**

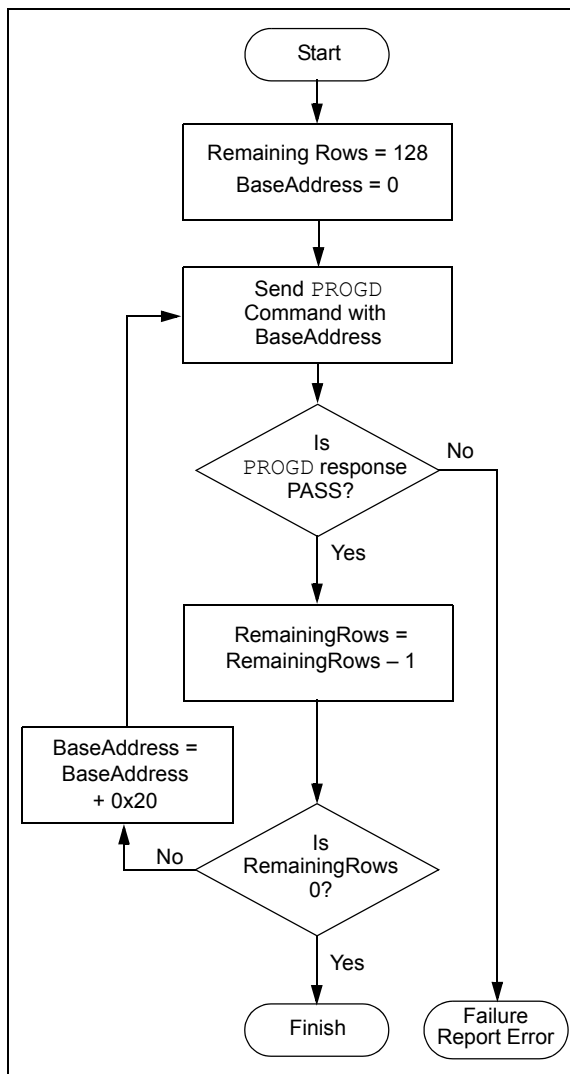
Device	Data EEPROM Size (Words)	Number of Rows
dsPIC30F2010	512	32
dsPIC30F2011	0	0
dsPIC30F2012	0	0
dsPIC30F3010	512	32
dsPIC30F3011	512	32
dsPIC30F3012	512	32
dsPIC30F3013	512	32
dsPIC30F3014	512	32
dsPIC30F4011	512	32
dsPIC30F4012	512	32
dsPIC30F4013	512	32
dsPIC30F5011	512	32
dsPIC30F5013	512	32
dsPIC30F5015	512	32
dsPIC30F5016	512	32
dsPIC30F6010	2048	128
dsPIC30F6010A	2048	128
dsPIC30F6011	1024	64
dsPIC30F6011A	1024	64
dsPIC30F6012	2048	128
dsPIC30F6012A	2048	128
dsPIC30F6013	1024	64
dsPIC30F6013A	1024	64
dsPIC30F6014	2048	128
dsPIC30F6014A	2048	128
dsPIC30F6015	2048	128

## 5.6.2 PROGRAMMING METHODOLOGY

The programming executive uses the `PROGD` command to program the data EEPROM. [Figure 5-4](#) illustrates the flowchart of the process. Firstly, the number of rows to program (RemainingRows) is based on the device size, and the destination address (BaseAddress) is set to '0'. In this example, 128 rows (2048 words) of data EEPROM will be programmed.

The first `PROGD` command programs the first row of data EEPROM. Once the command completes successfully, 'RemainingRows' is decremented by 1 and compared with 0. Since there are 127 more rows to program, 'BaseAddress' is incremented by 0x20 to point to the next row of data EEPROM. This process is then repeated until all 128 rows of data EEPROM are programmed.

**FIGURE 5-4: FLOWCHART FOR PROGRAMMING dsPIC30F6014A DATA EEPROM**



# dsPIC30F Flash Programming Specification

**TABLE 5-5: FOSC CONFIGURATION BITS DESCRIPTION FOR dsPIC30F4011/4012 AND dsPIC30F5011/5013**

Bit Field	Register	Description
FCKSM<1:0>	FOSC	<b>Clock Switching Mode</b> 1x = Clock switching is disabled, Fail-Safe Clock Monitor is disabled 01 = Clock switching is enabled, Fail-Safe Clock Monitor is disabled 00 = Clock switching is enabled, Fail-Safe Clock Monitor is enabled
FOS<1:0>	FOSC	<b>Oscillator Source Selection on POR</b> 11 = Primary Oscillator 10 = Internal Low-Power RC Oscillator 01 = Internal Fast RC Oscillator 00 = Low-Power 32 kHz Oscillator (Timer1 Oscillator)
FPR<3:0>	FOSC	<b>Primary Oscillator Mode</b> 1111 = ECIO w/PLL 16X – External Clock mode with 16X PLL. OSC2 pin is I/O 1110 = ECIO w/PLL 8X – External Clock mode with 8X PLL. OSC2 pin is I/O 1101 = ECIO w/PLL 4X – External Clock mode with 4X PLL. OSC2 pin is I/O 1100 = ECIO – External Clock mode. OSC2 pin is I/O 1011 = EC – External Clock mode. OSC2 pin is system clock output (Fosc/4) 1010 = FRC w/PLL 8x – Internal fast RC oscillator with 8x PLL. OSC2 pin is I/O 1001 = ERC – External RC Oscillator mode. OSC2 pin is system clock output (Fosc/4) 1000 = ERCIO – External RC Oscillator mode. OSC2 pin is I/O 0111 = XT w/PLL 16X – XT Crystal Oscillator mode with 16X PLL 0110 = XT w/PLL 8X – XT Crystal Oscillator mode with 8X PLL 0101 = XT w/PLL 4X – XT Crystal Oscillator mode with 4X PLL 0100 = XT – XT Crystal Oscillator mode (4 MHz-10 MHz crystal) 0011 = FRC w/PLL 16x – Internal fast RC oscillator with 16x PLL. OSC2 pin is I/O 0010 = HS – HS Crystal Oscillator mode (10 MHz-25 MHz crystal) 0001 = FRC w/PLL 4x – Internal fast RC oscillator with 4x PLL. OSC2 pin is I/O 0000 = XTL – XTL Crystal Oscillator mode (200 kHz-4 MHz crystal)

# dsPIC30F Flash Programming Specification

**TABLE 5-6: FOSC CONFIGURATION BITS DESCRIPTION FOR dsPIC30F2011/2012, dsPIC30F3010/3011/3012/3013/3014, dsPIC30F4013, dsPIC30F5015/5016, dsPIC30F6010A/6011A/6012A/6013A/6014A AND dsPIC30F6015**

Bit Field	Register	Description
FCKSM<1:0>	FOSC	<b>Clock Switching Mode</b> 1x = Clock switching is disabled, Fail-Safe Clock Monitor is disabled 01 = Clock switching is enabled, Fail-Safe Clock Monitor is disabled 00 = Clock switching is enabled, Fail-Safe Clock Monitor is enabled
FOS<2:0>	FOSC	<b>Oscillator Source Selection on POR</b> 111 = Primary Oscillator 110 = Reserved 101 = Reserved 100 = Reserved 011 = Reserved 010 = Internal Low-Power RC Oscillator 001 = Internal Fast RC Oscillator (no PLL) 000 = Low-Power 32 kHz Oscillator (Timer1 Oscillator)
FPR<4:0>	FOSC	<b>Primary Oscillator Mode (when FOS&lt;2:0&gt; = 111b)</b> 11xxx = Reserved (do not use) 10111 = HS/3 w/PLL 16X – HS/3 crystal oscillator with 16X PLL (10 MHz-25 MHz crystal) 10110 = HS/3 w/PLL 8X – HS/3 crystal oscillator with 8X PLL (10 MHz-25 MHz crystal) 10101 = HS/3 w/PLL 4X – HS/3 crystal oscillator with 4X PLL (10 MHz-25 MHz crystal) 10100 = Reserved (do not use) 10011 = HS/2 w/PLL 16X – HS/2 crystal oscillator with 16X PLL (10 MHz-25 MHz crystal) 10010 = HS/2 w/PLL 8X – HS/2 crystal oscillator with 8X PLL (10 MHz-25 MHz crystal) 10001 = HS/2 w/PLL 4X – HS/2 crystal oscillator with 4X PLL (10 MHz-25 MHz crystal) 10000 = Reserved (do not use) 01111 = ECIO w/PLL 16x – External clock with 16x PLL. OSC2 pin is I/O 01110 = ECIO w/PLL 8x – External clock with 8x PLL. OSC2 pin is I/O 01101 = ECIO w/PLL 4x – External clock with 4x PLL. OSC2 pin is I/O 01100 = Reserved (do not use) 01011 = Reserved (do not use) 01010 = FRC w/PLL 8x – Internal fast RC oscillator with 8x PLL. OSC2 pin is I/O 01001 = Reserved (do not use) 01000 = Reserved (do not use) 00111 = XT w/PLL 16X – XT crystal oscillator with 16X PLL 00110 = XT w/PLL 8X – XT crystal oscillator with 8X PLL 00101 = XT w/PLL 4X – XT crystal oscillator with 4X PLL 00100 = Reserved (do not use) 00011 = FRC w/PLL 16x – Internal fast RC oscillator with 8x PLL. OSC2 pin is I/O 00010 = Reserved (do not use) 00001 = FRC w/PLL 4x – Internal fast RC oscillator with 4x PLL. OSC2 pin is I/O 00000 = Reserved (do not use)

# dsPIC30F Flash Programming Specification

## 6.0 OTHER PROGRAMMING FEATURES

### 6.1 Erasing Memory

Memory is erased by using an `ERASEB`, `ERASED` or `ERASEP` command, as detailed in [Section 8.5 “Command Descriptions”](#). Code memory can be erased by row using `ERASEP`. Data EEPROM can be erased by row using `ERASED`. When memory is erased, the affected memory locations are set to ‘1’s.

`ERASEB` provides several Bulk Erase options. Performing a Chip Erase with the `ERASEB` command clears all code memory, data EEPROM and code protection registers. Alternatively, `ERASEB` can be used to selectively erase either all code memory or data EEPROM. Erase options are summarized in [Table 6-1](#).

**TABLE 6-1: ERASE OPTIONS**

Command	Affected Region
<code>ERASEB</code>	Entire chip <sup>(1)</sup> or all code memory or all data EEPROM, or erase by segment
<code>ERASED</code>	Specified rows of data EEPROM
<code>ERASEP</code> <sup>(2)</sup>	Specified rows of code memory

- Note 1:** The system operation Configuration registers and device ID registers are not erasable.
- 2:** `ERASEP` cannot be used to erase code-protect Configuration bits. These bits must be erased using `ERASEB`.

### 6.2 Modifying Memory

Instead of bulk-erasing the device before programming, it is possible that you may want to modify only a section of an already programmed device. In this situation, Chip Erase is not a realistic option.

Instead, you can erase selective rows of code memory and data EEPROM using `ERASEP` and `ERASED`, respectively. You can then reprogram the modified rows with the `PROGP` and `PROGD` command pairs. In these cases, when code memory is programmed, single-panel programming must be specified in the `PROGP` command.

For modification of Advanced Code Protection bits for a particular segment, the entire chip must first be erased with the `ERASEB` command. Alternatively, on devices that support Advanced Security, individual segments (code and/or data EEPROM) may be erased, by suitably changing the MS (Memory Select)

field in the `ERASEB` command. The code-protect Configuration bits can then be reprogrammed using the `PROGC` command.

**Note:** If read or write code protection is enabled for a segment, no modifications can be made to that segment until code protection is disabled. Code protection can only be disabled by performing a Chip Erase or by performing a Segment Erase operation for the required segment.

### 6.3 Reading Memory

The `READD` command reads the data EEPROM, Configuration bits and device ID of the device. This command only returns 16-bit data and operates on 16-bit registers. `READD` can be used to return the entire contents of data EEPROM.

The `READP` command reads the code memory of the device. This command only returns 24-bit data packed as described in [Section 8.3 “Packed Data Format”](#). `READP` can be used to read up to 32K instruction words of code memory.

**Note:** Reading an unimplemented memory location causes the programming executive to reset. All `READD` and `READP` commands **must** specify only valid memory locations.

### 6.4 Programming Executive Software Version

At times, it may be necessary to determine the version of programming executive stored in executive memory. The `QVER` command performs this function. See [Section 8.5.11 “QVER Command”](#) for more details about this command.

### 6.5 Data EEPROM Information in the Hexadecimal File

To allow portability of code, the programmer must read the data EEPROM information from the hexadecimal file. If data EEPROM information is not present, a simple warning message should be issued by the programmer. Similarly, when saving a hexadecimal file, all data EEPROM information must be included. An option to not include the data EEPROM information can be provided.

Microchip Technology Inc. believes that this feature is important for the benefit of the end customer.

# dsPIC30F Flash Programming Specification

## 8.5 Command Descriptions

All commands that are supported by the programming executive are described in [Section 8.5.1 “SCHECK Command”](#) through [Section 8.5.11 “QVER Command”](#).

### 8.5.1 SCHECK COMMAND

15	12	11	0
Opcode	Length		

Field	Description
Opcode	0x0
Length	0x1

The `SCHECK` command instructs the programming executive to do nothing, but generate a response. This command is used as a “sanity check” to verify that the programming executive is operational.

#### Expected Response (2 words):

0x1000  
0x0002

**Note:** This instruction is not required for programming, but is provided for development purposes only.

### 8.5.2 READD COMMAND

15	12	11	8	7	0
Opcode		Length			
Reserved0		N			
Reserved1			Addr_MSB		
Addr_LS					

Field	Description
Opcode	0x1
Length	0x4
Reserved0	0x0
N	Number of 16-bit words to read (max of 2048)
Reserved1	0x0
Addr_MSB	MSB of 24-bit source address
Addr_LS	LS 16 bits of 24-bit source address

The `READD` command instructs the programming executive to read N 16-bit words of memory starting from the 24-bit address specified by `Addr_MSB` and `Addr_LS`. This command can only be used to read 16-bit data. It can be used to read data EEPROM, Configuration registers and the device ID.

#### Expected Response (2+N words):

0x1100  
N + 2  
Data word 1  
...  
Data word N

**Note:** Reading unimplemented memory will cause the programming executive to reset.

# dsPIC30F Flash Programming Specification

## 8.5.3 READP COMMAND

15	12	11	8	7	0
Opcode		Length			
N					
Reserved			Addr_MSB		
Addr_LS					

Field	Description
Opcode	0x2
Length	0x4
N	Number of 24-bit instructions to read (max of 32768)
Reserved	0x0
Addr_MSB	MSB of 24-bit source address
Addr_LS	LS 16 bits of 24-bit source address

The **READP** command instructs the programming executive to read N 24-bit words of code memory starting from the 24-bit address specified by Addr\_MSB and Addr\_LS. This command can only be used to read 24-bit data. All data returned in response to this command uses the packed data format described in [Section 8.3 “Packed Data Format”](#).

### Expected Response (2 + 3 \* N/2 words for N even):

0x1200

2 + 3 \* N/2

Least significant program memory word 1

...

Least significant data word N

### Expected Response (4 + 3 \* (N – 1)/2 words for N odd):

0x1200

4 + 3 \* (N – 1)/2

Least significant program memory word 1

...

MSB of program memory word N (zero padded)

**Note:** Reading unimplemented memory will cause the programming executive to reset.

## 8.5.4 PROGD COMMAND

15	12	11	8	7	0
Opcode		Length			
Reserved			Addr_MSB		
Addr_LS					
D_1					
D_2					
...					
D_16					

Field	Description
Opcode	0x4
Length	0x13
Reserved	0x0
Addr_MSB	MSB of 24-bit destination address
Addr_LS	LS 16 bits of 24-bit destination address
D_1	16-bit data word 1
D_2	16-bit data word 2
...	16-bit data words 3 through 15
D_16	16-bit data word 16

The **PROGD** command instructs the programming executive to program one row of data EEPROM. The data to be programmed is specified by the 16 data words (D\_1, D\_2,..., D\_16) and is programmed to the destination address specified by Addr\_MSB and Addr\_LSB. The destination address should be a multiple of 0x20.

Once the row of data EEPROM has been programmed, the programming executive verifies the programmed data against the data in the command.

### Expected Response (2 words):

0x1400

0x0002

**Note:** Refer to [Table 5-3](#) for data EEPROM size information.

# dsPIC30F Flash Programming Specification

## 8.5.5 PROGP COMMAND

15	12	11	8	7	0
Opcode		Length			
Reserved			Addr_MSB		
Addr_LS					
D_1					
D_2					
...					
D_N					

Field	Description
Opcode	0x5
Length	0x33
Reserved	0x0
Addr_MSB	MSB of 24-bit destination address
Addr_LS	LS 16 bits of 24-bit destination address
D_1	16-bit data word 1
D_2	16-bit data word 2
...	16-bit data word 3 through 47
D_48	16-bit data word 48

The **PROGP** command instructs the programming executive to program one row of code memory (32 instruction words) to the specified memory address. Programming begins with the row address specified in the command. The destination address should be a multiple of 0x40.

The data to program to memory, located in command words D\_1 through D\_48, must be arranged using the packed instruction word format shown in [Figure 8-2](#).

After all data has been programmed to code memory, the programming executive verifies the programmed data against the data in the command.

### Expected Response (2 words):

0x1500  
0x0002

**Note:** Refer to [Table 5-2](#) for code memory size information.

## 8.5.6 PROGC COMMAND

15	12	11	8	7	0
Opcode		Length			
Reserved			Addr_MSB		
Addr_LS					
Data					

Field	Description
Opcode	0x6
Length	0x4
Reserved	0x0
Addr_MSB	MSB of 24-bit destination address
Addr_LS	LS 16 bits of 24-bit destination address
Data	Data to program

The **PROGC** command programs data to the specified Configuration register and verifies the programming. Configuration registers are 16 bits wide, and this command allows one Configuration register to be programmed.

### Expected Response (2 words):

0x1600  
0x0002

**Note:** This command can only be used for programming Configuration registers.



# dsPIC30F Flash Programming Specification

## 8.5.7 ERASEB COMMAND

15	12	11		2	0
Opcode		Length			
Reserved					MS

Field	Description
Opcode	0x7
Length	0x2
Reserved	0x0
MS	Select memory to erase: 0x0 = All Code in General Segment 0x1 = All Data EEPROM in General Segment 0x2 = All Code and Data EEPROM in General Segment, interrupt vectors and FGS Configuration register 0x3 = Full Chip Erase 0x4 = All Code and Data EEPROM in Boot, Secure and General Segments, and FBS, FSS and FGS Configuration registers 0x5 = All Code and Data EEPROM in Secure and General Segments, and FSS and FGS Configuration registers 0x6 = All Data EEPROM in Boot Segment 0x7 = All Data EEPROM in Secure Segment

The **ERASEB** command performs a Bulk Erase. The MS field selects the memory to be bulk erased, with options for erasing Code and/or Data EEPROM in individual memory segments.

When Full Chip Erase is selected, the following memory regions are erased:

- All code memory (even if code-protected)
- All data EEPROM
- All code-protect Configuration registers

Only the executive code memory, Unit ID, device ID and Configuration registers that are not code-protected remain intact after a Chip Erase.

### Expected Response (2 words):

0x1700  
0x0002

**Note:** A Full Chip Erase cannot be performed in low-voltage programming systems ( $V_{DD}$  less than 4.5 volts). **ERASED** and **ERASEP** must be used to erase code memory, executive memory and data memory. Alternatively, individual Segment Erase operations may be performed.

## 8.5.8 ERASED COMMAND

15	12	11		8	7		0
Opcode		Length					
Num_Rows				Addr_MSB			
Addr_LS							

Field	Description
Opcode	0x8
Length	0x3
Num_Rows	Number of rows to erase (max of 128)
Addr_MSB	MSB of 24-bit base address
Addr_LS	LS 16 bits of 24-bit base address

The **ERASED** command erases the specified number of rows of data EEPROM from the specified base address. The specified base address must be a multiple of 0x20. Since the data EEPROM is mapped to program space, a 24-bit base address must be specified.

After the erase is performed, all targeted bytes of data EEPROM will contain 0xFF.

### Expected Response (2 words):

0x1800  
0x0002

**Note:** The **ERASED** command cannot be used to erase the Configuration registers or device ID. Code-protect Configuration registers can only be erased with the **ERASEB** command, while the device ID is read-only.

# dsPIC30F Flash Programming Specification

## 9.2.3 QE\_Code FIELD

The QE\_Code is a byte in the first word of the response. This byte is used to return data for query commands, and error codes for all other commands.

When the programming executive processes one of the two query commands (`QBLANK` or `QVER`), the returned opcode is always PASS and the QE\_Code holds the query response data. The format of the QE\_Code for both queries is shown in [Table 9-3](#).

**TABLE 9-3: QE\_Code FOR QUERIES**

Query	QE_Code
QBLANK	0x0F = Code memory and data EEPROM are NOT blank 0xF0 = Code memory and data EEPROM are blank
QVER	0xMN, where programming executive software version = M.N (i.e., 0x32 means software version 3.2)

When the programming executive processes any command other than a Query, the QE\_Code represents an error code. Supported error codes are shown in [Table 9-4](#). If a command is successfully processed, the returned QE\_Code is set to 0x0, which indicates that there was no error in the command processing. If the verify of the programming for the `PROGD`, `PROGP` or `PROGC` command fails, the QE\_Code is set to 0x1. For all other programming executive errors, the QE\_Code is 0x2.

**TABLE 9-4: QE\_Code FOR NON-QUERY COMMANDS**

QE_Code	Description
0x0	No error
0x1	Verify failed
0x2	Other error

## 9.2.4 RESPONSE LENGTH

The response length indicates the length of the programming executive's response in 16-bit words. This field includes the 2 words of the response header.

With the exception of the response for the `READD` and `READP` commands, the length of each response is only 2 words.

The response to the `READD` command is  $N + 2$  words, where  $N$  is the number of words specified in the `READD` command.

The response to the `READP` command uses the packed instruction word format described in [Section 8.3 "Packed Data Format"](#). When reading an odd number of program memory words ( $N$  odd), the response to the `READP` command is  $(3 \cdot (N + 1)/2 + 2)$  words. When reading an even number of program memory words ( $N$  even), the response to the `READP` command is  $(3 \cdot N/2 + 2)$  words.

# dsPIC30F Flash Programming Specification

## 11.0 ICSP™ MODE

### 11.1 ICSP Mode

ICSP mode is a special programming protocol that allows you to read and write to the dsPIC30F programming executive. The ICSP mode is the second (and slower) method used to program the device. This mode also has the ability to read the contents of executive memory to determine whether the programming executive is present. This capability is accomplished by applying control codes and instructions serially to the device using pins PGC and PGD.

In ICSP mode, the system clock is taken from the PGC pin, regardless of the device's oscillator Configuration bits. All instructions are first shifted serially into an internal buffer, then loaded into the Instruction register and executed. No program fetching occurs from internal memory. Instructions are fed in 24 bits at a time. PGD is used to shift data in and PGC is used as both the serial shift clock and the CPU execution clock.

Data is transmitted on the rising edge and latched on the falling edge of PGC. For all data transmissions, the Least Significant bit (LSb) is transmitted first.

**Note 1:** During ICSP operation, the operating frequency of PGC must not exceed 5 MHz.

**2:** Because ICSP is slower, it is recommended that only Enhanced ICSP (E-ICSP) mode be used for device programming, as described in [Section 5.1 "Overview of the Programming Process"](#).

### 11.2 ICSP Operation

Upon entry into ICSP mode, the CPU is idle. Execution of the CPU is governed by an internal state machine. A 4-bit control code is clocked in using PGC and PGD, and this control code is used to command the CPU (see [Table 11-1](#)).

The SIX control code is used to send instructions to the CPU for execution, while the REGOUT control code is used to read data out of the device via the VISI register. The operation details of ICSP mode are provided in [Section 11.2.1 "SIX Serial Instruction Execution"](#) and [Section 11.2.2 "REGOUT Serial Instruction Execution"](#).

**TABLE 11-1: CPU CONTROL CODES IN ICSP™ MODE**

4-bit Control Code	Mnemonic	Description
0000b	SIX	Shift in 24-bit instruction and execute.
0001b	REGOUT	Shift out the VISI register.
0010b-1111b	N/A	Reserved.

#### 11.2.1 SIX SERIAL INSTRUCTION EXECUTION

The SIX control code allows execution of dsPIC30F assembly instructions. When the SIX code is received, the CPU is suspended for 24 clock cycles as the instruction is then clocked into the internal buffer. Once the instruction is shifted in, the state machine allows it to be executed over the next four clock cycles. While the received instruction is executed, the state machine simultaneously shifts in the next 4-bit command (see [Figure 11-2](#)).

**Note 1:** Coming out of the ICSP entry sequence, the first 4-bit control code is always forced to SIX and a forced NOP instruction is executed by the CPU. Five additional PGC clocks are needed on start-up, thereby resulting in a 9-bit SIX command instead of the normal 4-bit SIX command. After the forced SIX is clocked in, ICSP operation resumes as normal (the next 24 clock cycles load the first instruction word to the CPU). See [Figure 11-1](#) for details.

**2:** TBLRDH, TBLRDL, TBLWTH and TBLWTL instructions must be followed by a NOP instruction.

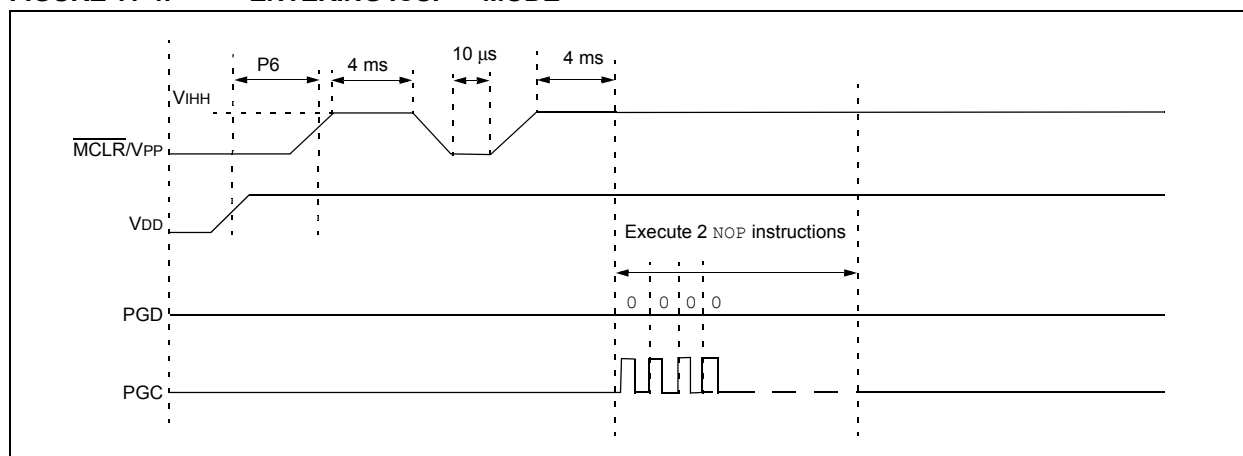
# dsPIC30F Flash Programming Specification

## 11.3 Entering ICSP Mode

The ICSP mode is entered by holding PGC and PGD low, raising MCLR/VPP to VIH (high voltage), and then performing additional steps as illustrated in [Figure 11-4](#).

- Note 1:** The sequence that places the device into ICSP mode places all unused I/O pins to the high-impedance state.
- 2:** Once ICSP mode is entered, the PC is set to 0x0 (the Reset vector).
- 3:** Before leaving the Reset vector, execute two `GOTO` instructions, followed by a single `NOP` instruction must be executed.

**FIGURE 11-4: ENTERING ICSP™ MODE**



# dsPIC30F Flash Programming Specification

## 11.4 Flash Memory Programming in ICSP Mode

Programming in ICSP mode is described in [Section 11.4.1 “Programming Operations”](#) through [Section 11.4.3 “Starting and Stopping a Programming Cycle”](#). Step-by-step procedures are described in [Section 11.5 “Erasing Program Memory in Normal-Voltage Systems”](#) through [Section 11.13 “Reading the Application ID Word”](#). All programming operations must use serial execution, as described in [Section 11.2 “ICSP Operation”](#).

### 11.4.1 PROGRAMMING OPERATIONS

Flash memory write and erase operations are controlled by the NVMCON register. Programming is performed by setting NVMCON to select the type of erase operation ([Table 11-2](#)) or write operation ([Table 11-3](#)), writing a key sequence to enable the programming and initiating the programming by setting the WR control bit, NVMCON<15>.

In ICSP mode, all programming operations are externally timed. An external 2 ms delay must be used between setting the WR control bit and clearing the WR control bit to complete the programming operation.

**TABLE 11-2: NVMCON ERASE OPERATIONS**

NVMCON Value	Erase Operation
0x407F	Erase all code memory, data memory (does not erase UNIT ID).
0x4075	Erase 1 row (16 words) of data EEPROM.
0x4074	Erase 1 word of data EEPROM.
0x4072	Erase all executive memory.
0x4071	Erase 1 row (32 instruction words) from 1 panel of code memory.
0x406E	Erase Boot Secure and General Segments, then erase FBS, FSS and FGS configuration registers.
0x4066	Erase all Data EEPROM allocated to Boot Segment.
0x405E	Erase Secure and General Segments, then erase FSS and FGS configuration registers.
0x4056	Erase all Data EEPROM allocated to Secure Segment.
0x404E	Erase General Segment, then erase FGS configuration register.
0x4046	Erase all Data EEPROM allocated to General Segment.

**TABLE 11-3: NVMCON WRITE OPERATIONS**

NVMCON Value	Write Operation
0x4008	Write 1 word to configuration memory.
0x4005	Write 1 row (16 words) to data memory.
0x4004	Write 1 word to data memory.
0x4001	Write 1 row (32 instruction words) into 1 panel of program memory.

### 11.4.2 UNLOCKING NVMCON FOR PROGRAMMING

Writes to the WR bit (NVMCON<15>) are locked to prevent accidental programming from taking place. Writing a key sequence to the NVMKEY register unlocks the WR bit and allows it to be written to. The unlock sequence is performed as follows:

```
MOV    #0x55, W8
MOV    W8, NVMKEY
MOV    #0xAA, W9
MOV    W9, NVMKEY
```

**Note:** Any working register, or working register pair, can be used to write the unlock sequence.

### 11.4.3 STARTING AND STOPPING A PROGRAMMING CYCLE

Once the unlock key sequence has been written to the NVMKEY register, the WR bit (NVMCON<15>) is used to start and stop an erase or write cycle. Setting the WR bit initiates the programming cycle. Clearing the WR bit terminates the programming cycle.

All erase and write cycles must be externally timed. An external delay must be used between setting and clearing the WR bit. Starting and stopping a programming cycle is performed as follows:

```
BSET    NVMCON, #WR
<Wait 2 ms>
BCLR    NVMCON, #WR
```

## 11.5 Erasing Program Memory in Normal-Voltage Systems

The procedure for erasing program memory (all code memory, data memory, executive memory and code-protect bits) consists of setting NVMCON to 0x407F, unlocking NVMCON for erasing and then executing the programming cycle. This method of bulk erasing program memory only works for systems where VDD is between 4.5 volts and 5.5 volts. The method for erasing program memory for systems with a lower VDD (3.0 volts–4.5 volts) is described in [Section 6.1 “Erasing Memory”](#).

# dsPIC30F Flash Programming Specification

## 11.9 Writing Data EEPROM

The procedure for writing data EEPROM is very similar to the procedure for writing code memory, except that fewer words are programmed in each operation. When writing data EEPROM, one row of data EEPROM is programmed at a time. Each row consists of sixteen 16-bit data words. Since fewer words are programmed

during each operation, only working registers W0:W3 are used as temporary holding registers for the data to be programmed.

Table 11-9 shows the ICSP programming details for writing data EEPROM. Note that a different NVMCON value is required to write to data EEPROM, and that the TBLPAG register is hard-coded to 0x7F (the upper byte address of all locations of data EEPROM).

**TABLE 11-9: SERIAL INSTRUCTION EXECUTION FOR WRITING DATA EEPROM**

Command (Binary)	Data (Hexadecimal)	Description
<b>Step 1: Exit the Reset vector.</b>		
0000	040100	GOTO 0x100
0000	040100	GOTO 0x100
0000	000000	NOP
<b>Step 2: Set the NVMCON to write 16 data words.</b>		
0000	24005A	MOV #0x4005, W10
0000	883B0A	MOV W10, NVMCON
<b>Step 3: Initialize the write pointer (W7) for TBLWT instruction.</b>		
0000	2007F0	MOV #0x7F, W0
0000	880190	MOV W0, TBLPAG
0000	2xxxx7	MOV #<DestinationAddress15:0>, W7
<b>Step 4: Load W0:W3 with the next 4 data words to program.</b>		
0000	2xxxx0	MOV #<WORD0>, W0
0000	2xxxx1	MOV #<WORD1>, W1
0000	2xxxx2	MOV #<WORD2>, W2
0000	2xxxx3	MOV #<WORD3>, W3
<b>Step 5: Set the read pointer (W6) and load the (next set of) write latches.</b>		
0000	EB0300	CLR W6
0000	000000	NOP
0000	BB1BB6	TBLWTL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BB1BB6	TBLWTL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BB1BB6	TBLWTL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
0000	BB1BB6	TBLWTL [W6++], [W7++]
0000	000000	NOP
0000	000000	NOP
<b>Step 6: Repeat steps 4-5 four times to load the write latches for 16 data words.</b>		

# dsPIC30F Flash Programming Specification

TABLE 11-9: SERIAL INSTRUCTION EXECUTION FOR WRITING DATA EEPROM (CONTINUED)

Command (Binary)	Data (Hexadecimal)	Description
<b>Step 7: Unlock the NVMCON for writing.</b>		
0000	200558	MOV #0x55, W8
0000	883B38	MOV W8, NVMKEY
0000	200AA9	MOV #0xAA, W9
0000	883B39	MOV W9, NVMKEY
<b>Step 8: Initiate the write cycle.</b>		
0000	A8E761	BSET NVMCON, #WR
0000	000000	NOP
0000	000000	NOP
—	—	Externally time 'P12a' ms (see <a href="#">Section 13.0 “AC/DC Characteristics and Timing Requirements”</a> )
0000	000000	NOP
0000	000000	NOP
0000	A9E761	BCLR NVMCON, #WR
0000	000000	NOP
0000	000000	NOP
<b>Step 9: Reset device internal PC.</b>		
0000	040100	GOTO 0x100
0000	000000	NOP
<b>Step 10: Repeat steps 2-9 until all data memory is programmed.</b>		

# dsPIC30F Flash Programming Specification

**TABLE 12-2: READING EXECUTIVE MEMORY (CONTINUED)**

Command (Binary)	Data (Hexadecimal)	Description
<b>Step 4:</b> Output W0:W5 using the VISI register and REGOUT command.		
0000	883C20	MOV W0, VISI
0000	000000	NOP
0001	—	Clock out contents of VISI register
0000	883C21	MOV W1, VISI
0000	000000	NOP
0001	—	Clock out contents of VISI register
0000	883C22	MOV W2, VISI
0000	000000	NOP
0001	—	Clock out contents of VISI register
0000	883C23	MOV W3, VISI
0000	000000	NOP
0001	—	Clock out contents of VISI register
0000	883C24	MOV W4, VISI
0000	000000	NOP
0001	—	Clock out contents of VISI register
0000	883C25	MOV W5, VISI
0000	000000	NOP
0001	—	Clock out contents of VISI register
<b>Step 5:</b> Reset the device internal PC.		
0000	040100	GOTO 0x100
0000	000000	NOP
<b>Step 6:</b> Repeat Steps 3-5 until all 736 instruction words of executive memory are read.		



# dsPIC30F Flash Programming Specification

**TABLE 13-1: AC/DC CHARACTERISTICS (CONTINUED)**

AC/DC CHARACTERISTICS			Standard Operating Conditions (unless otherwise stated) Operating Temperature: 25° C is recommended			
Param. No.	Sym	Characteristic	Min	Max	Units	Conditions
P9b	TDLY5	Delay between PGD ↓ by programming executive to PGD released by programming executive	15	—	μs	—
P10	TDLY6	Delay between PGD released by programming executive to first PGC ↑ of response	5	—	μs	—
P11	TDLY7	Delay between clocking out response words	10	—	μs	—
P12a	TPROG	Row Programming cycle time	1	4	ms	ICSP mode
P12b	TPROG	Row Programming cycle time	0.8	2.6	ms	Enhanced ICSP mode
P13a	TERA	Bulk/Row Erase cycle time	1	4	ms	ICSP mode
P13b	TERA	Bulk/Row Erase cycle time	0.8	2.6	ms	Enhanced ICSP mode

# dsPIC30F Flash Programming Specification

## APPENDIX A: DEVICE-SPECIFIC INFORMATION

### A.1 Checksum Computation

The checksum computation is described in [Section 6.8 “Checksum Computation”](#). [Table A-1](#) shows how this 16-bit computation can be made for each dsPIC30F device. Computations for read code protection are shown both enabled and disabled. The checksum values assume that the Configuration registers are also erased. However, when code protection is enabled, the value of the FGS register is assumed to be 0x5.

### A.2 dsPIC30F5011 and dsPIC30F5013

#### A.2.1 ICSP PROGRAMMING

The dsPIC30F5011 and dsPIC30F5013 processors require that the FBS and FSS registers be programmed with 0x0000 before the device is chip erased. The steps to perform this action are shown in [Table 11-4](#).

#### A.2.2 ENHANCED ICSP PROGRAMMING

The dsPIC30F5011 and dsPIC30F5013 processors require that the FBS and FSS registers be programmed with 0x0000 using the `PROGC` command before the `ERASEB` command is used to erase the chip.

**TABLE A-1: CHECKSUM COMPUTATION**

Device	Read Code Protection	Checksum Computation	Erased Value	Value with 0xAAAAAA at 0x0 and Last Code Address
dsPIC30F2010	Disabled	CFGB+SUM(0:001FFF)	0xD406	0xD208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F2011	Disabled	CFGB+SUM(0:001FFF)	0xD406	0xD208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F2012	Disabled	CFGB+SUM(0:001FFF)	0xD406	0xD208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F3010	Disabled	CFGB+SUM(0:003FFF)	0xA406	0xA208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F3011	Disabled	CFGB+SUM(0:003FFF)	0xA406	0xA208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F3012	Disabled	CFGB+SUM(0:003FFF)	0xA406	0xA208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F3013	Disabled	CFGB+SUM(0:003FFF)	0xA406	0xA208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F3014	Disabled	CFGB+SUM(0:003FFF)	0xA406	0xA208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F4011	Disabled	CFGB+SUM(0:007FFF)	0x4406	0x4208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F4012	Disabled	CFGB+SUM(0:007FFF)	0x4406	0x4208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F4013	Disabled	CFGB+SUM(0:007FFF)	0x4406	0x4208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F5011	Disabled	CFGB+SUM(0:00AFFF)	0xFC06	0xFA08
	Enabled	CFGB	0x0404	0x0404
dsPIC30F5013	Disabled	CFGB+SUM(0:00AFFF)	0xFC06	0xFA08
	Enabled	CFGB	0x0404	0x0404
dsPIC30F5015	Disabled	CFGB+SUM(0:00AFFF)	0xFC06	0xFA08
	Enabled	CFGB	0x0404	0x0404

#### Item Description:

**SUM(a:b)** = Byte sum of locations a to b inclusive (all 3 bytes of code memory)

**CFGB** = **Configuration Block (masked)** = Byte sum of ((FOSC&0xC10F) + (FWDTE&0x803F) + (FBORPOR&0x87B3) + (FBS&0x310F) + (FSS&0x330F) + (FGS&0x0007) + (FICD&0xC003))

# dsPIC30F Flash Programming Specification

**TABLE A-1: CHECKSUM COMPUTATION (CONTINUED)**

Device	Read Code Protection	Checksum Computation	Erased Value	Value with 0xAAAAAA at 0x0 and Last Code Address
dsPIC30F5016	Disabled	CFGB+SUM(0:00AFFF)	0xFC06	0xFA08
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6010	Disabled	CFGB+SUM(0:017FFF)	0xC406	0xC208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6010A	Disabled	CFGB+SUM(0:017FFF)	0xC406	0xC208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6011	Disabled	CFGB+SUM(0:015FFF)	0xF406	0xF208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6011A	Disabled	CFGB+SUM(0:015FFF)	0xF406	0xF208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6012	Disabled	CFGB+SUM(0:017FFF)	0xC406	0xC208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6012A	Disabled	CFGB+SUM(0:017FFF)	0xC406	0xC208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6013	Disabled	CFGB+SUM(0:015FFF)	0xF406	0xF208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6013A	Disabled	CFGB+SUM(0:015FFF)	0xF406	0xF208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6014	Disabled	CFGB+SUM(0:017FFF)	0xC406	0xC208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6014A	Disabled	CFGB+SUM(0:017FFF)	0xC406	0xC208
	Enabled	CFGB	0x0404	0x0404
dsPIC30F6015	Disabled	CFGB+SUM(0:017FFF)	0xC406	0xC208
	Enabled	CFGB	0x0404	0x0404

**Item Description:**

**SUM(a:b)** = Byte sum of locations a to b inclusive (all 3 bytes of code memory)

**CFGB** = **Configuration Block (masked)** = Byte sum of ((FOSC&0xC10F) + (FWDT&0x803F) + (FBORPOR&0x87B3) + (FBS&0x310F) + (FSS&0x330F) + (FGS&0x0007) + (FICD&0xC003))

# dsPIC30F Flash Programming Specification

---

## APPENDIX B: HEX FILE FORMAT

Flash programmers process the standard HEX format used by the Microchip development tools. The format supported is the Intel® HEX 32 Format (INHX32). Please refer to Appendix A in the “*MPASM User's Guide*” (DS33014) for more information about hex file formats.

The basic format of the hex file is:

```
:BBAAAATTTHHHH...HHHHCC
```

Each data record begins with a 9-character prefix and always ends with a 2-character checksum. All records begin with ':' regardless of the format. The individual elements are described below.

- **BB** - is a two-digit hexadecimal byte count representing the number of data bytes that appear on the line. Divide this number by two to get the number of words per line.
- **AAAA** - is a four-digit hexadecimal address representing the starting address of the data record. Format is high byte first followed by low byte. The address is doubled because this format only supports 8-bits. Divide the value by two to find the real device address.
- **TT** - is a two-digit record type that will be '00' for data records, '01' for end-of-file records and '04' for extended-address record.
- **HHHH** - is a four-digit hexadecimal data word. Format is low byte followed by high byte. There will be  $BB/2$  data words following **TT**.
- **CC** - is a two-digit hexadecimal checksum that is the two's complement of the sum of all the preceding bytes in the line record.

Because the Intel hex file format is byte-oriented, and the 16-bit program counter is not, program memory sections require special treatment. Each 24-bit program word is extended to 32 bits by inserting a so-called “phantom byte”. Each program memory address is multiplied by 2 to yield a byte address.

As an example, a section that is located at 0x100 in program memory will be represented in the hex file as 0x200.

The hex file will be produced with the following contents:

```
:020000040000fa
:040200003322110096
:00000001FF
```

Notice that the data record (line 2) has a load address of 0200, while the source code specified address 0x100. Note also that the data is represented in “little-endian” format, meaning the Least Significant Byte (LSB) appears first. The phantom byte appears last, just before the checksum.

## Worldwide Sales and Service

### AMERICAS

**Corporate Office**  
2355 West Chandler Blvd.  
Chandler, AZ 85224-6199  
Tel: 480-792-7200  
Fax: 480-792-7277  
Technical Support:  
<http://support.microchip.com>  
Web Address:  
[www.microchip.com](http://www.microchip.com)

**Atlanta**  
Duluth, GA  
Tel: 678-957-9614  
Fax: 678-957-1455

**Boston**  
Westborough, MA  
Tel: 774-760-0087  
Fax: 774-760-0088

**Chicago**  
Itasca, IL  
Tel: 630-285-0071  
Fax: 630-285-0075

**Cleveland**  
Independence, OH  
Tel: 216-447-0464  
Fax: 216-447-0643

**Dallas**  
Addison, TX  
Tel: 972-818-7423  
Fax: 972-818-2924

**Detroit**  
Farmington Hills, MI  
Tel: 248-538-2250  
Fax: 248-538-2260

**Kokomo**  
Kokomo, IN  
Tel: 765-864-8360  
Fax: 765-864-8387

**Los Angeles**  
Mission Viejo, CA  
Tel: 949-462-9523  
Fax: 949-462-9608

**Santa Clara**  
Santa Clara, CA  
Tel: 408-961-6444  
Fax: 408-961-6445

**Toronto**  
Mississauga, Ontario,  
Canada  
Tel: 905-673-0699  
Fax: 905-673-6509

### ASIA/PACIFIC

**Asia Pacific Office**  
Suites 3707-14, 37th Floor  
Tower 6, The Gateway  
Harbour City, Kowloon  
Hong Kong  
Tel: 852-2401-1200  
Fax: 852-2401-3431

**Australia - Sydney**  
Tel: 61-2-9868-6733  
Fax: 61-2-9868-6755

**China - Beijing**  
Tel: 86-10-8528-2100  
Fax: 86-10-8528-2104

**China - Chengdu**  
Tel: 86-28-8665-5511  
Fax: 86-28-8665-7889

**China - Chongqing**  
Tel: 86-23-8980-9588  
Fax: 86-23-8980-9500

**China - Hong Kong SAR**  
Tel: 852-2401-1200  
Fax: 852-2401-3431

**China - Nanjing**  
Tel: 86-25-8473-2460  
Fax: 86-25-8473-2470

**China - Qingdao**  
Tel: 86-532-8502-7355  
Fax: 86-532-8502-7205

**China - Shanghai**  
Tel: 86-21-5407-5533  
Fax: 86-21-5407-5066

**China - Shenyang**  
Tel: 86-24-2334-2829  
Fax: 86-24-2334-2393

**China - Shenzhen**  
Tel: 86-755-8203-2660  
Fax: 86-755-8203-1760

**China - Wuhan**  
Tel: 86-27-5980-5300  
Fax: 86-27-5980-5118

**China - Xian**  
Tel: 86-29-8833-7252  
Fax: 86-29-8833-7256

**China - Xiamen**  
Tel: 86-592-2388138  
Fax: 86-592-2388130

**China - Zhuhai**  
Tel: 86-756-3210040  
Fax: 86-756-3210049

### ASIA/PACIFIC

**India - Bangalore**  
Tel: 91-80-3090-4444  
Fax: 91-80-3090-4123

**India - New Delhi**  
Tel: 91-11-4160-8631  
Fax: 91-11-4160-8632

**India - Pune**  
Tel: 91-20-2566-1512  
Fax: 91-20-2566-1513

**Japan - Yokohama**  
Tel: 81-45-471- 6166  
Fax: 81-45-471-6122

**Korea - Daegu**  
Tel: 82-53-744-4301  
Fax: 82-53-744-4302

**Korea - Seoul**  
Tel: 82-2-554-7200  
Fax: 82-2-558-5932 or  
82-2-558-5934

**Malaysia - Kuala Lumpur**  
Tel: 60-3-6201-9857  
Fax: 60-3-6201-9859

**Malaysia - Penang**  
Tel: 60-4-227-8870  
Fax: 60-4-227-4068

**Philippines - Manila**  
Tel: 63-2-634-9065  
Fax: 63-2-634-9069

**Singapore**  
Tel: 65-6334-8870  
Fax: 65-6334-8850

**Taiwan - Hsin Chu**  
Tel: 886-3-6578-300  
Fax: 886-3-6578-370

**Taiwan - Kaohsiung**  
Tel: 886-7-213-7830  
Fax: 886-7-330-9305

**Taiwan - Taipei**  
Tel: 886-2-2500-6610  
Fax: 886-2-2508-0102

**Thailand - Bangkok**  
Tel: 66-2-694-1351  
Fax: 66-2-694-1350

### EUROPE

**Austria - Wels**  
Tel: 43-7242-2244-39  
Fax: 43-7242-2244-393

**Denmark - Copenhagen**  
Tel: 45-4450-2828  
Fax: 45-4485-2829

**France - Paris**  
Tel: 33-1-69-53-63-20  
Fax: 33-1-69-30-90-79

**Germany - Munich**  
Tel: 49-89-627-144-0  
Fax: 49-89-627-144-44

**Italy - Milan**  
Tel: 39-0331-742611  
Fax: 39-0331-466781

**Netherlands - Druenen**  
Tel: 31-416-690399  
Fax: 31-416-690340

**Spain - Madrid**  
Tel: 34-91-708-08-90  
Fax: 34-91-708-08-91

**UK - Wokingham**  
Tel: 44-118-921-5869  
Fax: 44-118-921-5820